

◆ OVERVIEW

QL63H5S-A/B/C is a MOCVD grown 635nm band *InGaAlP* laser diode with quantum well structure. It's an attractive light source, with a typical light output power of 20mW for optoelectronic devices such as Optical Leveler and Modules.

◆ APPLICATION

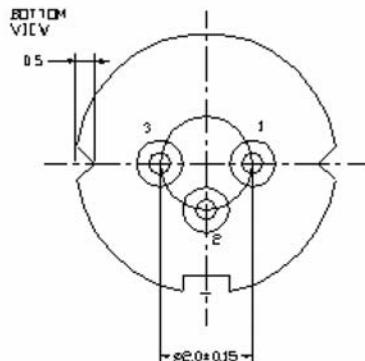
- Bar Code Scanner
- Laser Module

◆ FEATURES

- Visible Light Output : $\lambda_p = 635$ nm
- Optical Power Output : 20mW CW
- Package Type : TO-18 (5.6mm ϕ)
- Built-in Photo Diode for Monitoring Laser Diode

◆ ELECTRICAL CONNECTION

Bottom View



Pin Configuration

A	LD cathode, PD anode (Fig. 1)
B	LD , PD anode (Fig. 2)
C	LD anode, PD cathode (Fig. 3)

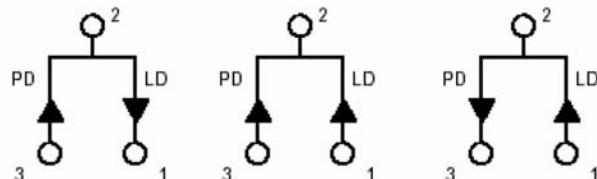


Fig. 1

QL63H5SA

Fig. 2

QL63H5SB

Fig. 3

QL63H5SC

◆ ABSOLUTE MAXIMUM RATING at $T_c=25^\circ\text{C}$

Items	Symbols	Values	Unit
Optical Output Power	P	24	mW
Laser Diode Reverse Voltage	V	2	V
Photo Diode Reverse Voltage	V	30	V
Operating Temperature	T_{opr}	$-10 \sim +50$	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-40 \sim +85$	$^\circ\text{C}$

◆ ELECTRICAL and OPTICAL CHARACTERISTICS at $T_c=25^\circ\text{C}$ ¹⁾⁽²⁾

Items	Symbols	Min.	Typ.	Max.	Unit	Condition
Optical Output Power	P_o	-	20	-	mW	-
Threshold Current	I_{th}	-	30	50	mA	$P_o=20\text{mW}$
Operating Current	I_{op}	-	60	80	mA	$P_o=20\text{mW}$
Operating Voltage	V_{op}	-	2.3	2.6	V	$P_o=20\text{mW}$
Lasing Wavelength	λ_p	630	639	645	nm	$P_o=20\text{mW}$
Beam Divergence ³⁾	$\theta_{ }$	6	8	11	deg	$P_o=20\text{mW}$
	θ_{\perp}	25	30	35	deg	$P_o=20\text{mW}$
Beam Angle	$\Delta\theta_{ }$	-	-	± 2.0	deg	$P_o=20\text{mW}$
	$\Delta\theta_{\perp}$	-	-	± 3.0	deg	$P_o=20\text{mW}$
Monitor Current	I_m	0.05	0.25	0.7	mA	$P_o=20\text{mW}$
Optical Distance	$\Delta X, \Delta Y, \Delta Z$	-	-	± 60	μm	-

1) Initial values

2) All above values are evaluated with measuring apparatus

3) Full angle at half maximum

NOTICE : QL63H5S-A/B/C to be operated on APC

The above product specifications are subject to change without notice.

◆ PACKAGE DIMENSION

